

## SMT810

## High Performance Infrared TOP IR LED

SMT810 consists of an AlGaAs LED mounted on the lead frame as TOP LED package and is 10mW typical of output power.

It emits a spectral band of radiation at 810nm.

♦ Outer dimension (Unit:mm)

◆ Specifications

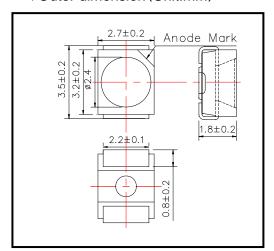
1) Product Name TOP IR LED 2) Type No. SMT810

3) Chip

(1) Chip Material AlGaAs(2) Peak Wavelength 810nm typ.

4) Package

(1) Lead Frame Die Silver Plated(2) Package Resin PPA Resin(3) Lens Epoxy Resin



## ♦ Absolute Maximum Rating

ltem	Symbol	Maximum Rated Value	Unit	Ambient Temperature	
Power Dissipation	Po	190	mW	Ta=25°C	
Forward Current	lF	100	mΑ	Ta=25°C	
Pulse Forward Current	lfp	500	mΑ	Ta=25°C	
Reverse Voltage	VR	5	V	Ta=25°C	
Operating Temperature	Topr	-20 ~ +80	°C		
Storage Temperature	Тsтg	-30 ~ +80	°C		
Soldering Temperature	Tsol	240	°C		

<sup>‡</sup>Pulse Forward Current condition: Duty=1% and Pulse Width=10us.

◆ Electro-Optical Characteristics [Ta=25°C]

Item	Symbol	Condition	Minimum	Typical	Maximum	Unit
Forward Voltage	VF	Ir=50mA		1.60	1.80	V
Reverse Current	lr	Vr=5V			10	uA
Total Radiated Power	Po	IF=50mA	5.0	10.0		mW
Radiant Intensity	ΙE	IF=50mA	3.0	6.0		mW/sr
Peak Wavelength	λР	I==50mA		810		nm
Half Width	Δλ	Ir=50mA		40		nm
Viewing Half Angle	θ 1/2	Ir=50mA		±55		deg.
Rise Time	tr	Ir=50mA		60		ns
Fall Time	tf	IF=50mA		40		ns

<sup>‡</sup>Total Radiated Power is measured by Photodyne #500

<sup>‡</sup>Soldering condition: Soldering condition must be completed within 3 seconds at 230°C

<sup>‡</sup>Radiant Intensity is measured by Tektronix J-6512.